

**FIG. 1**

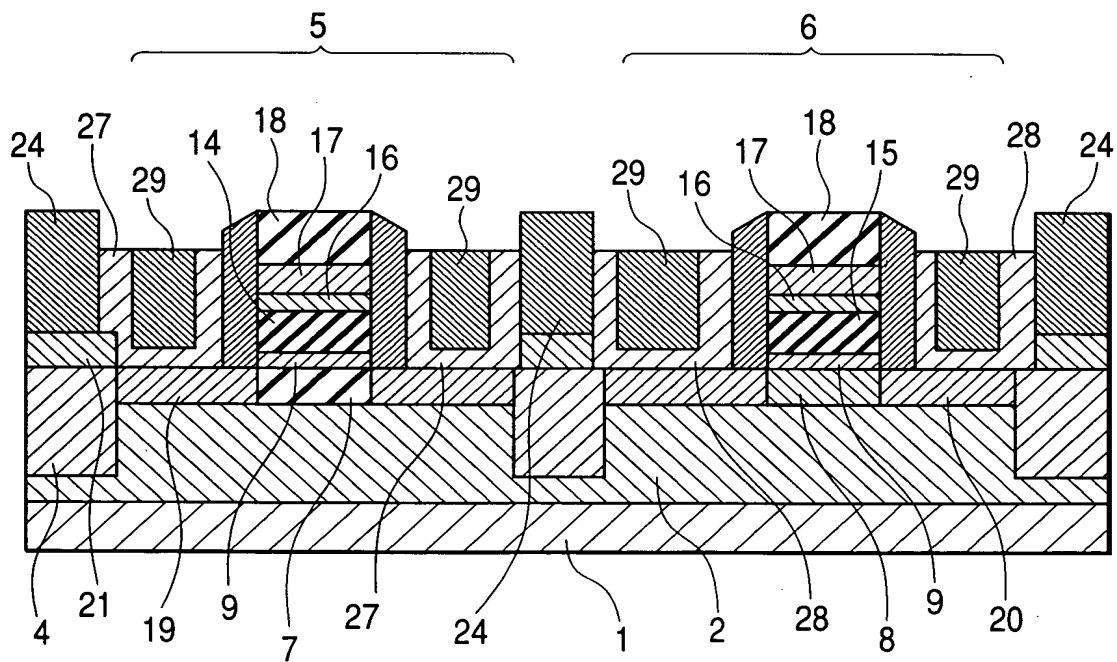
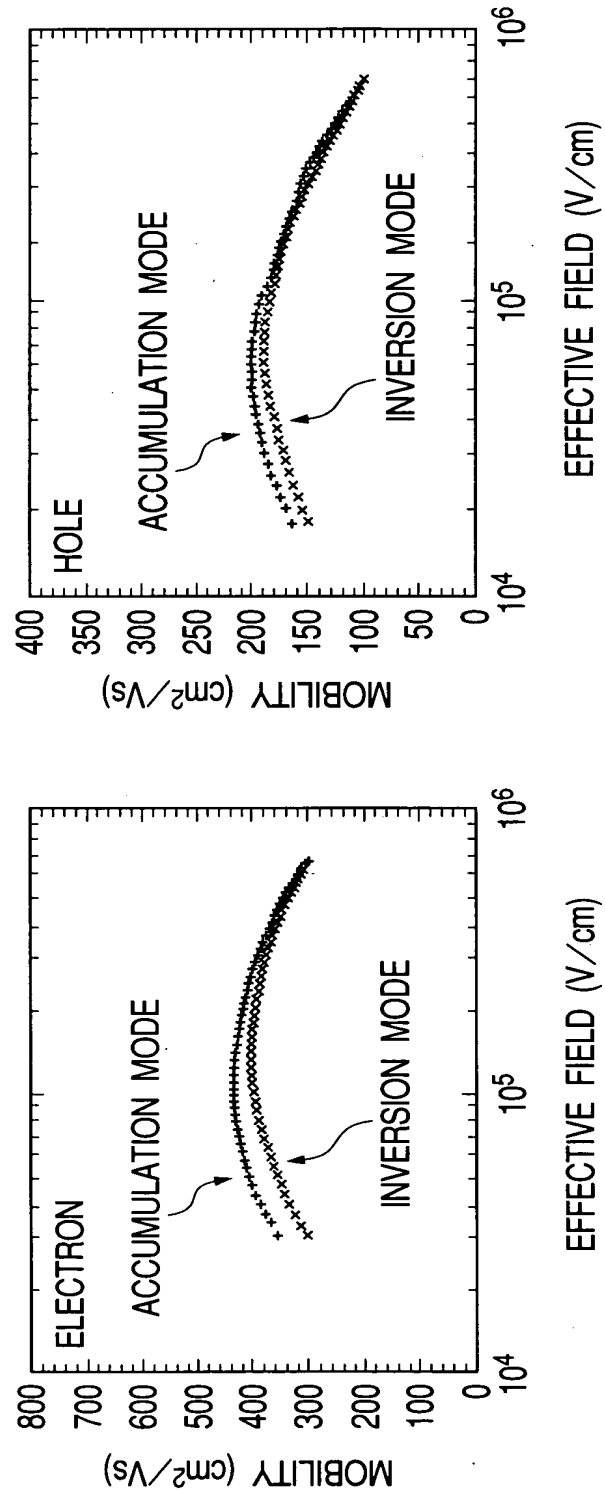
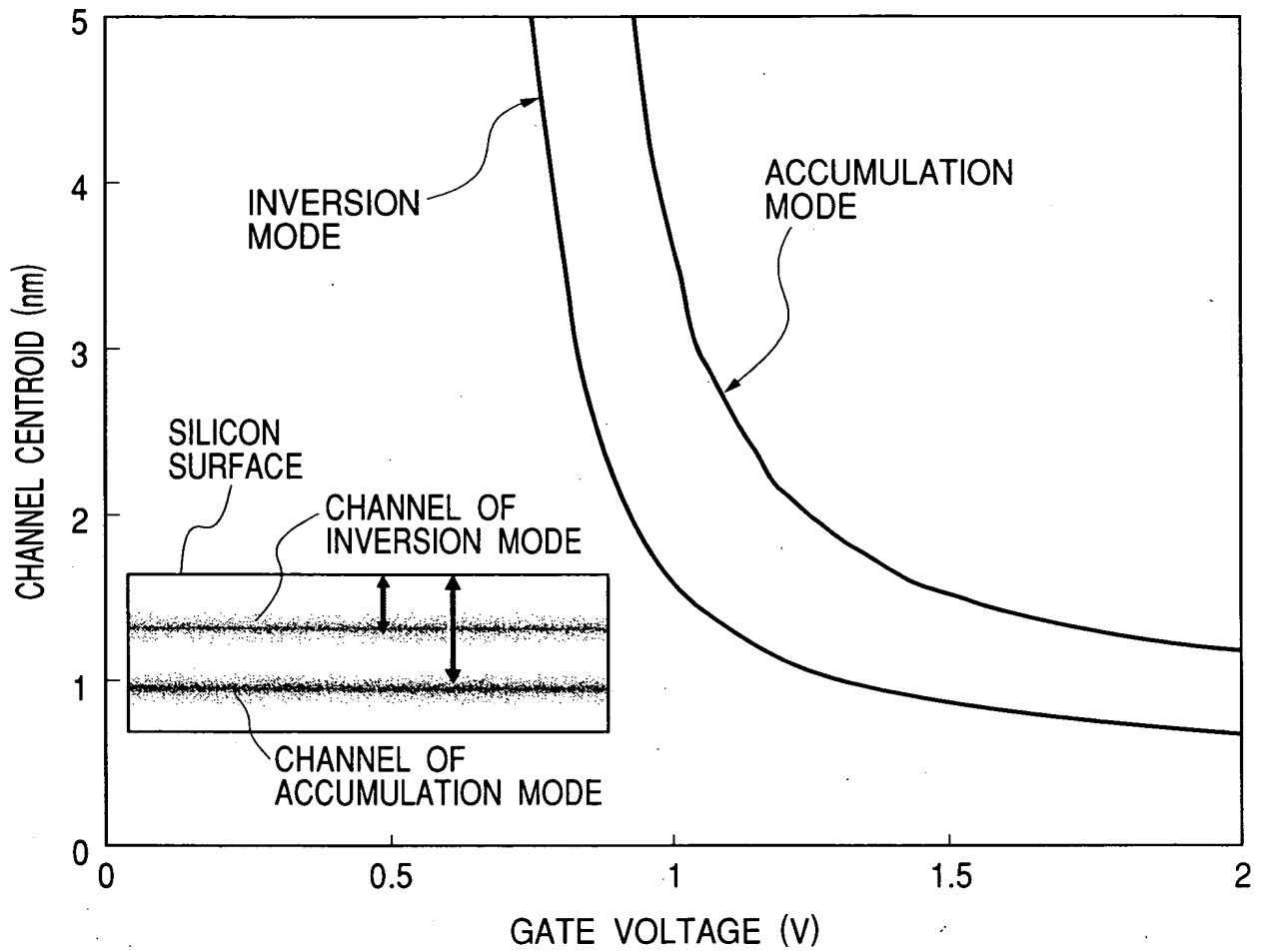


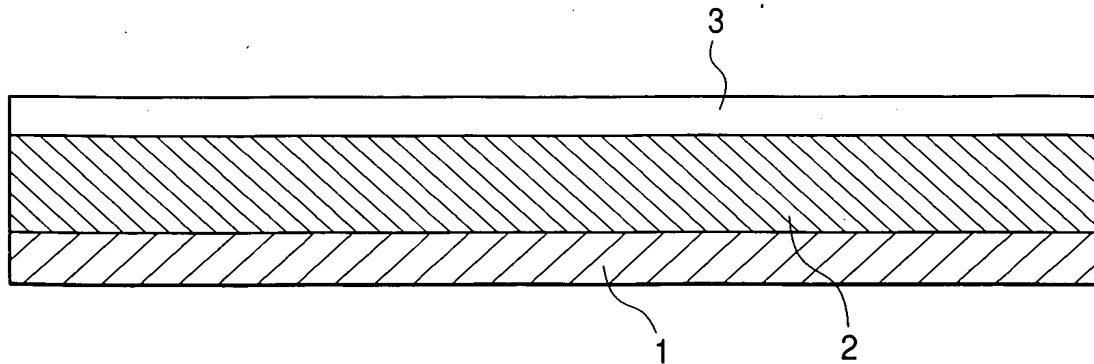
FIG. 2



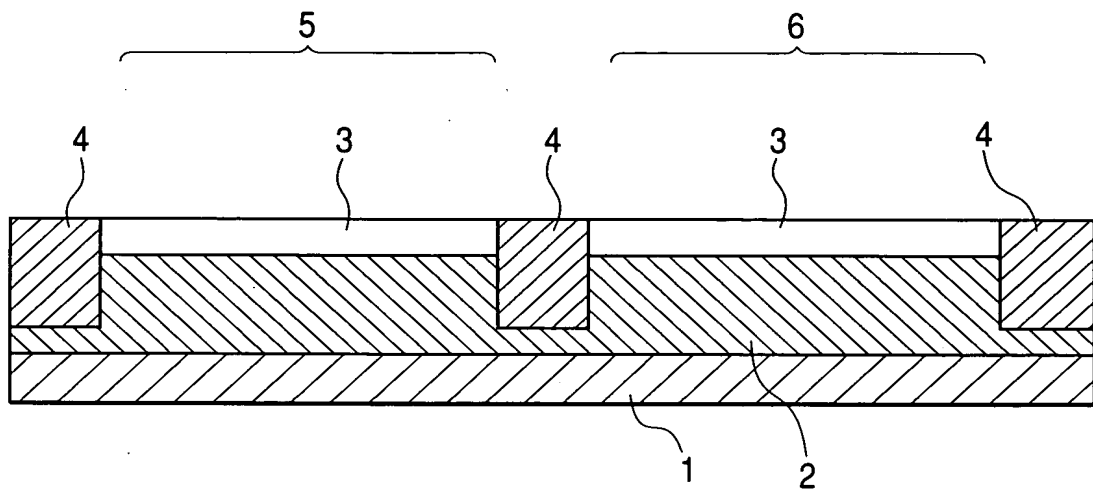
**FIG. 3**



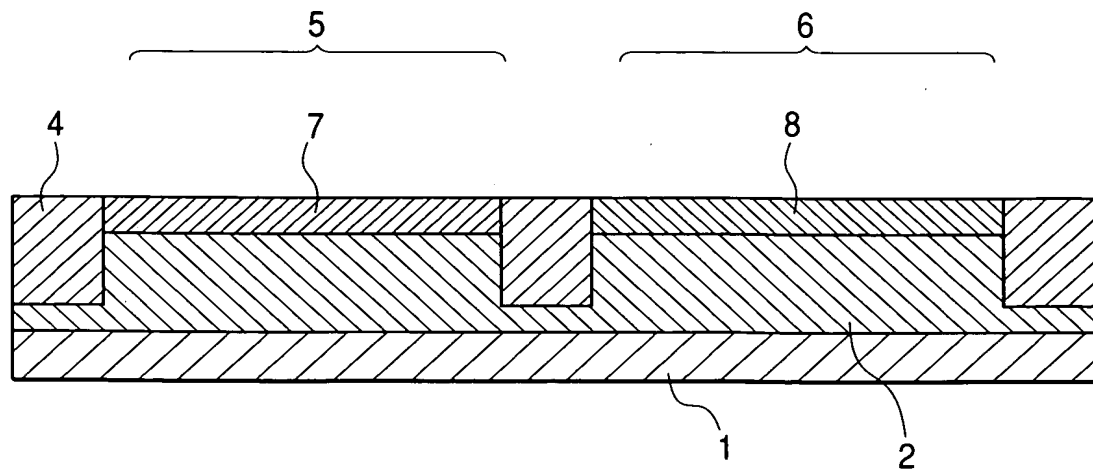
**FIG. 4**



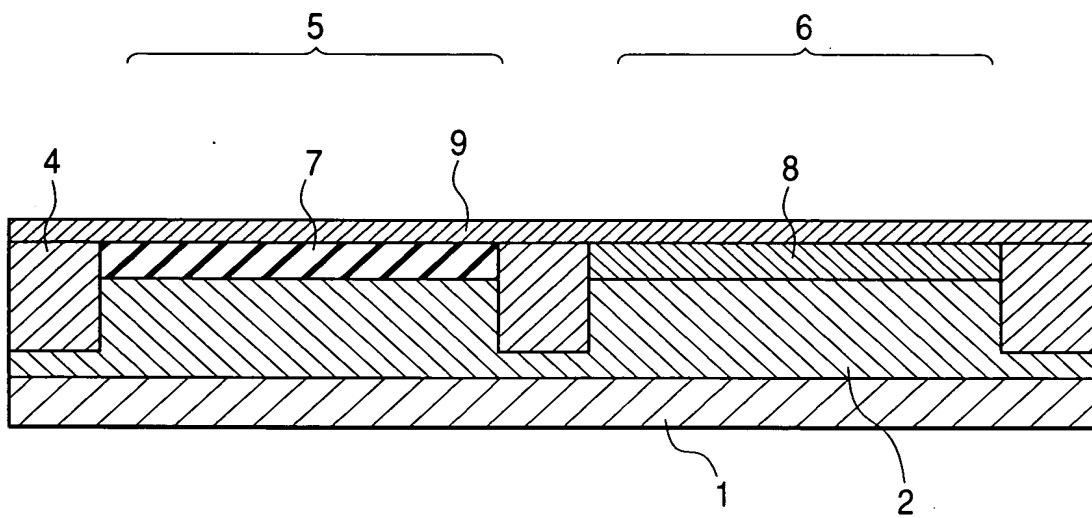
**FIG. 5**



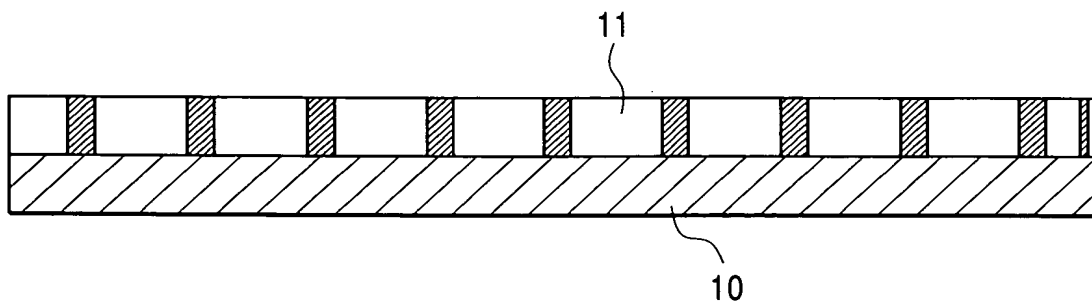
**FIG. 6**



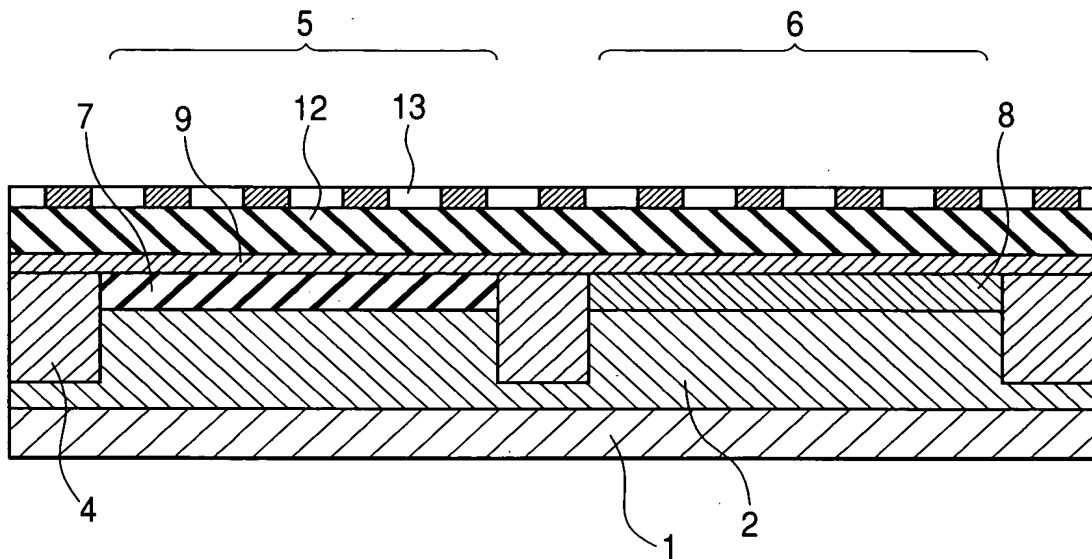
**FIG. 7**



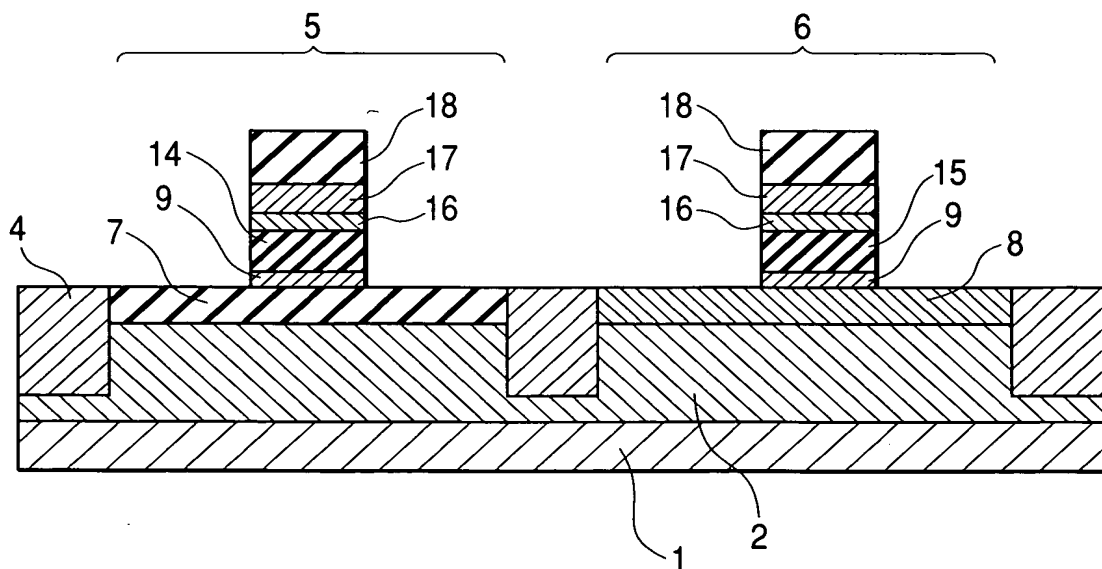
**FIG. 8**



**FIG. 9**

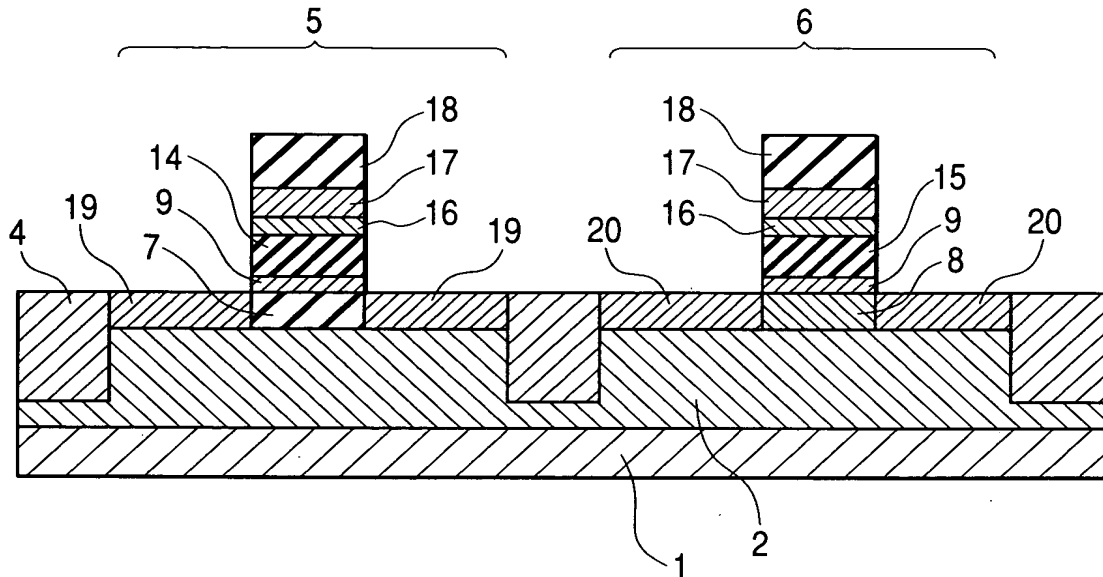


**FIG. 10**

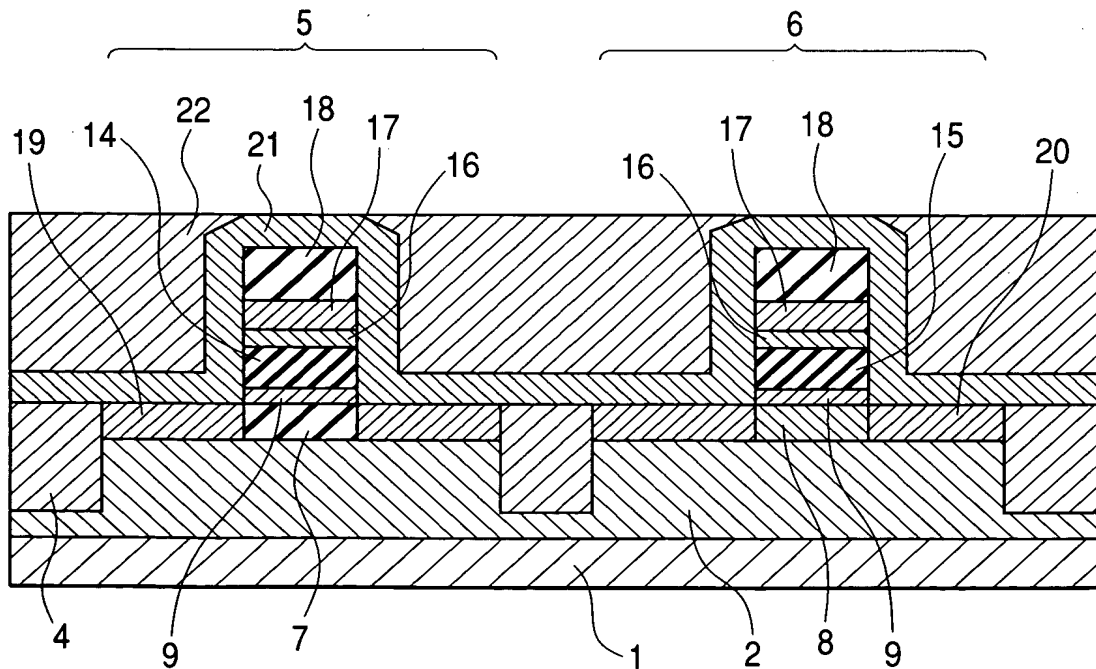


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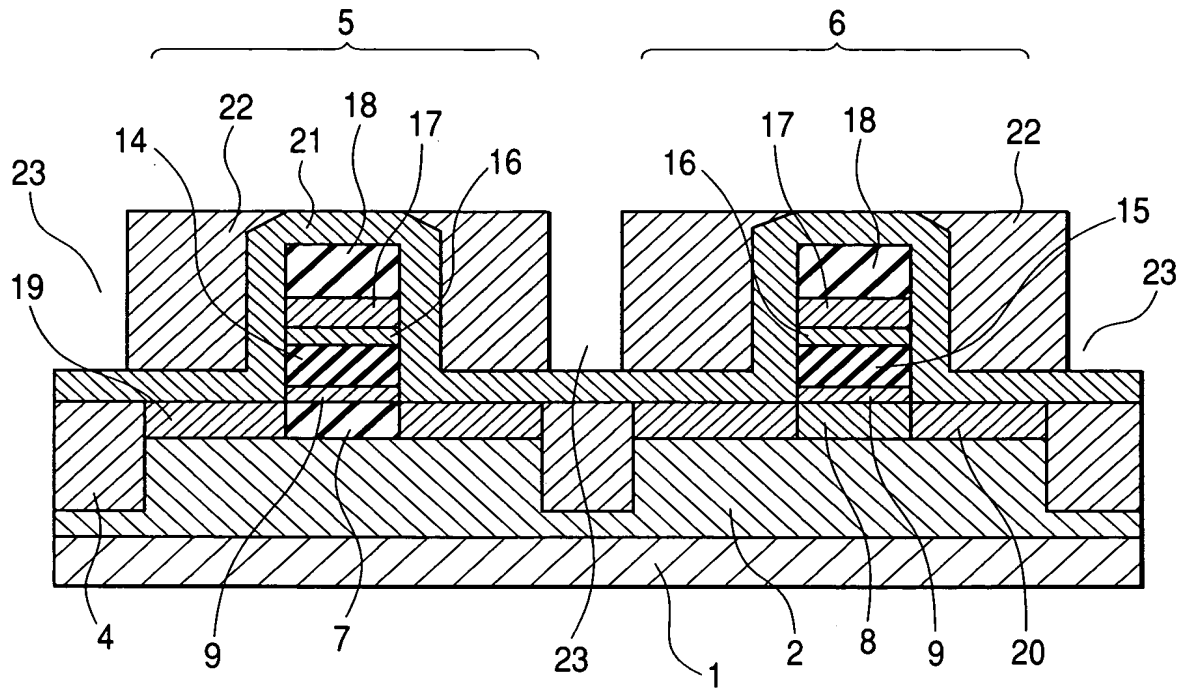
**FIG. 11**



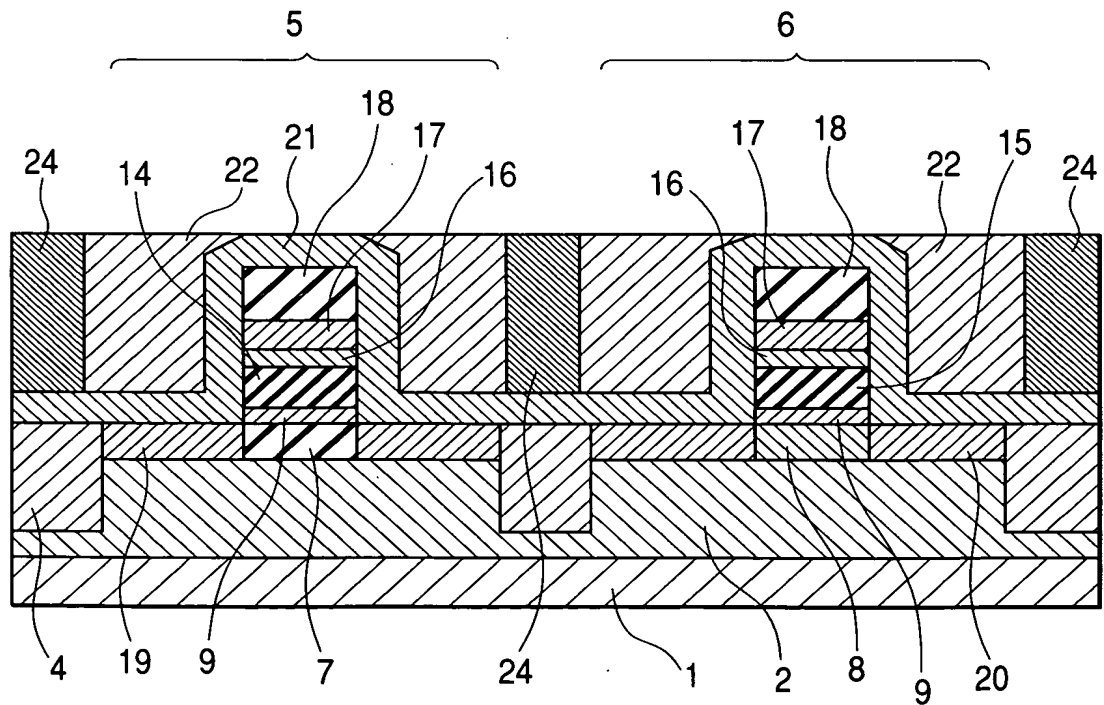
**FIG. 12**



**FIG. 13**

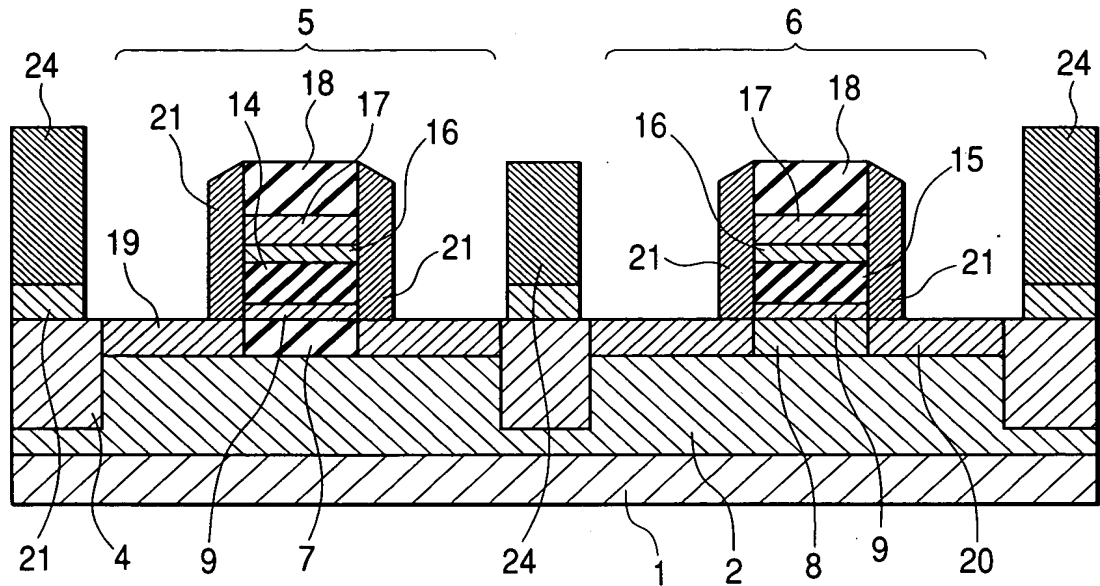


**FIG. 14**

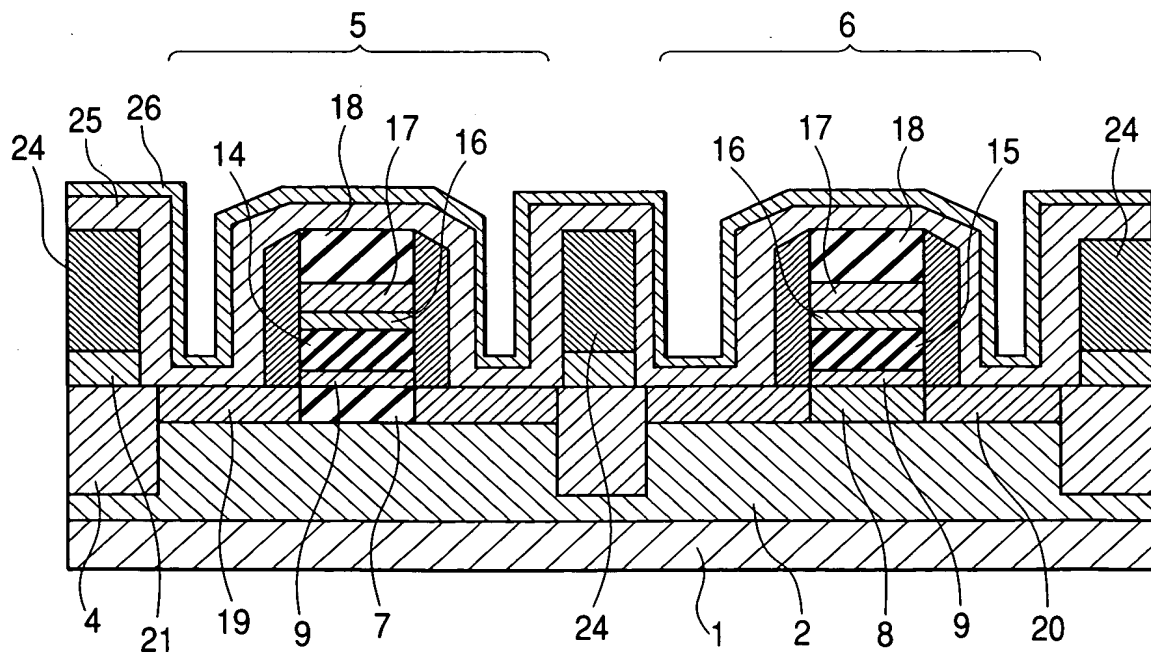




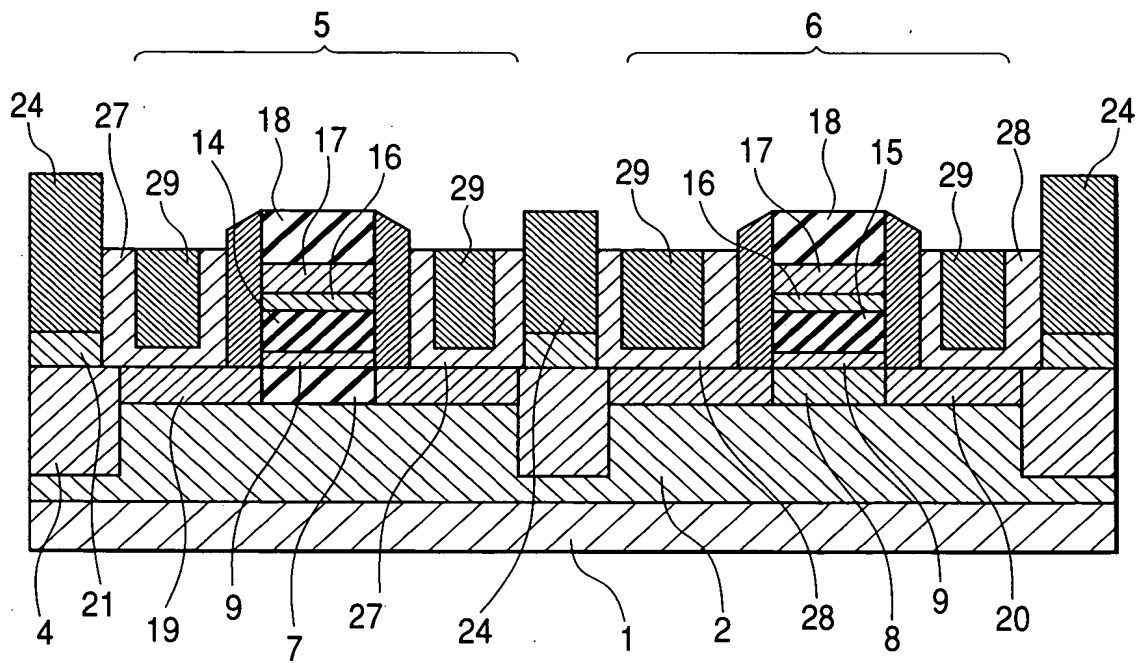
**FIG. 15**



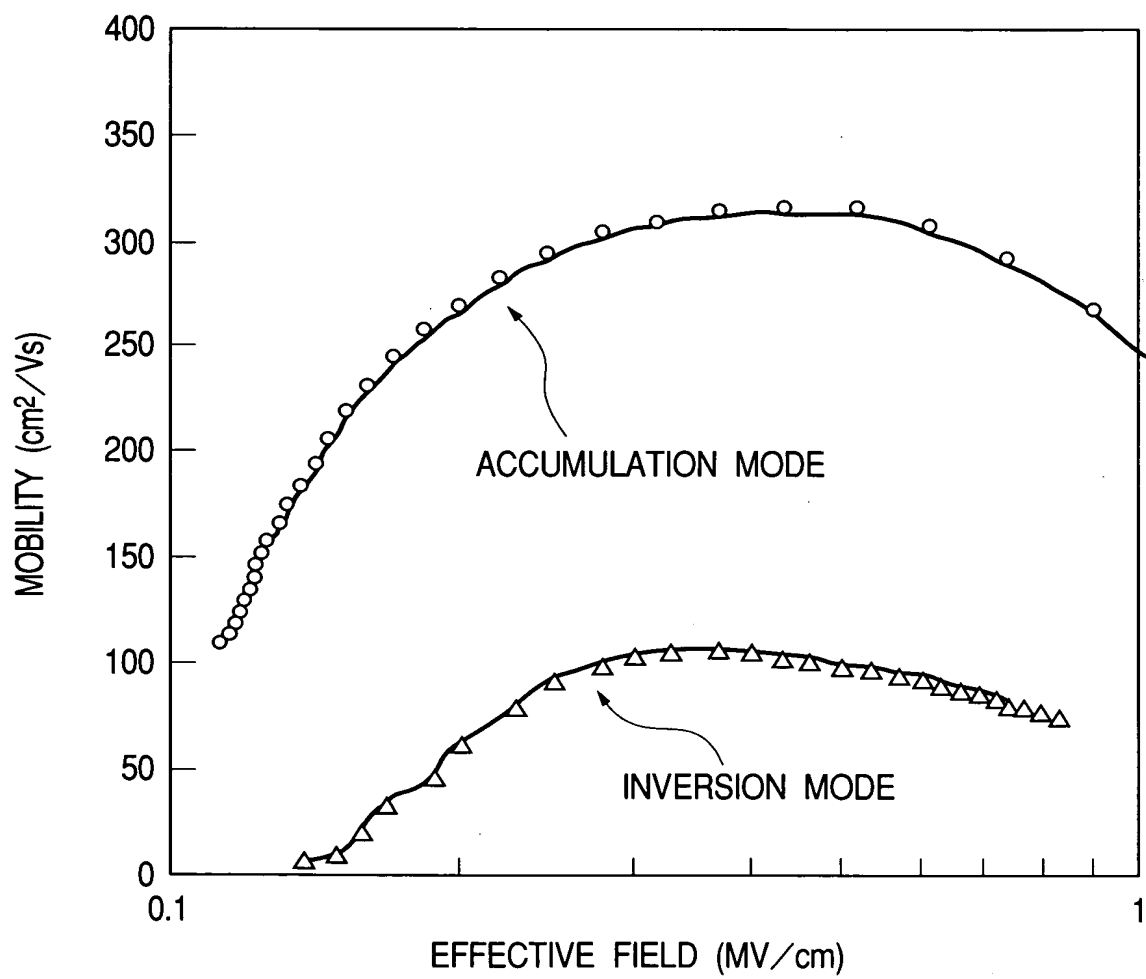
**FIG. 16**



**FIG. 17**

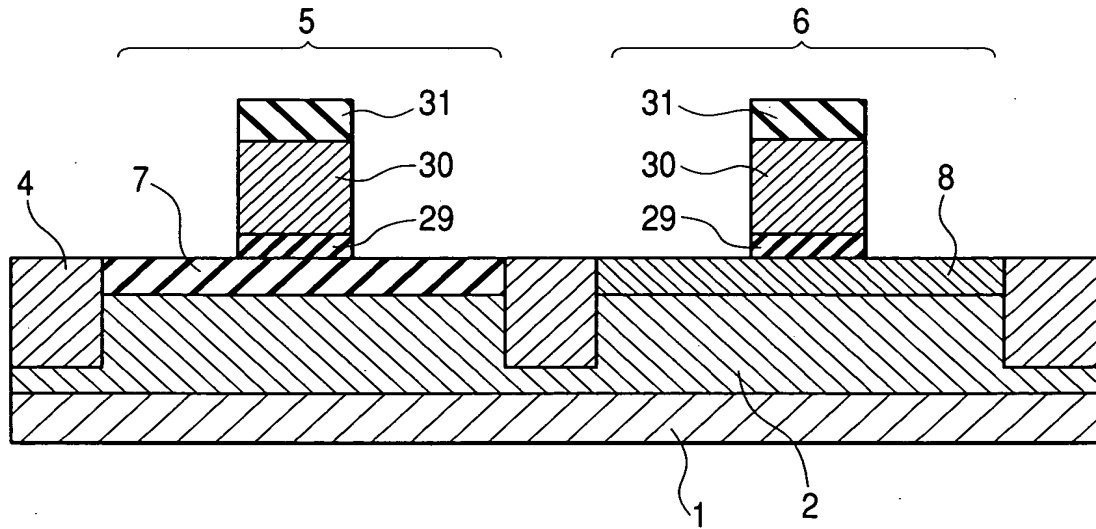


**FIG. 18**

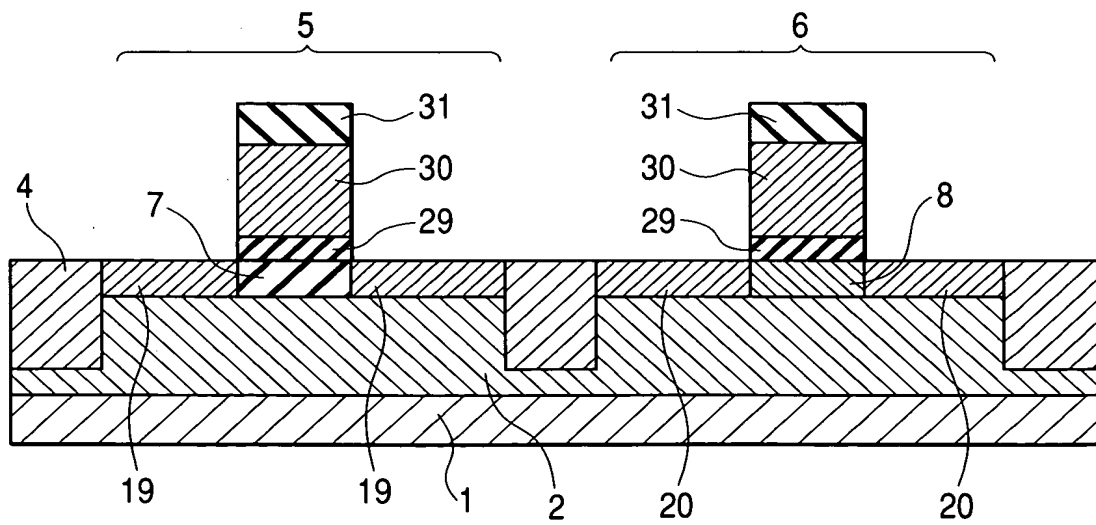


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**FIG. 19**



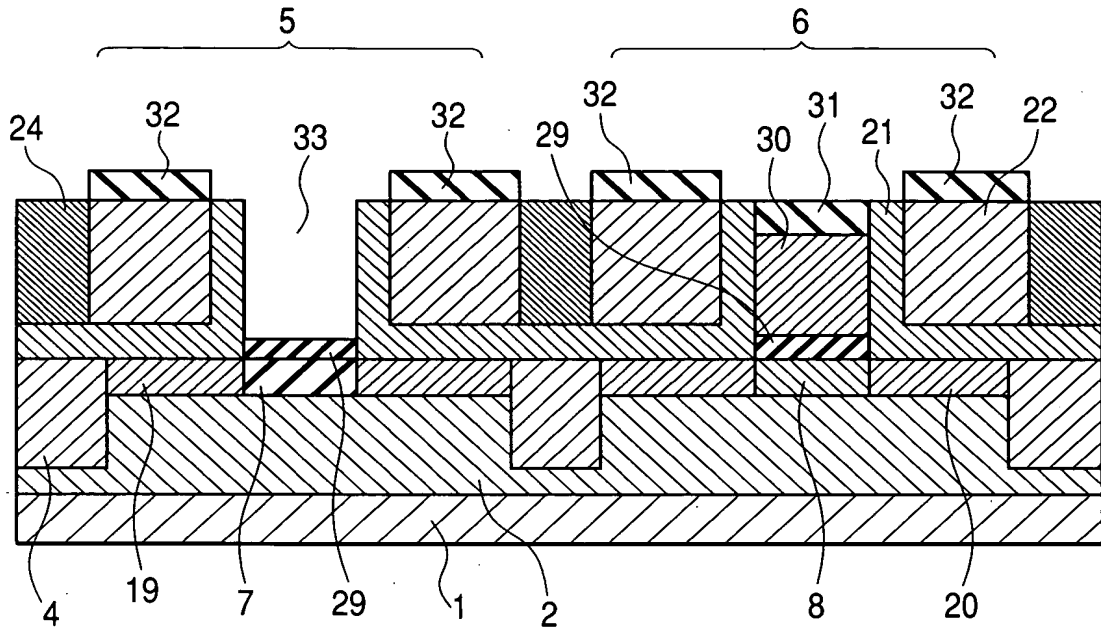
**FIG. 20**



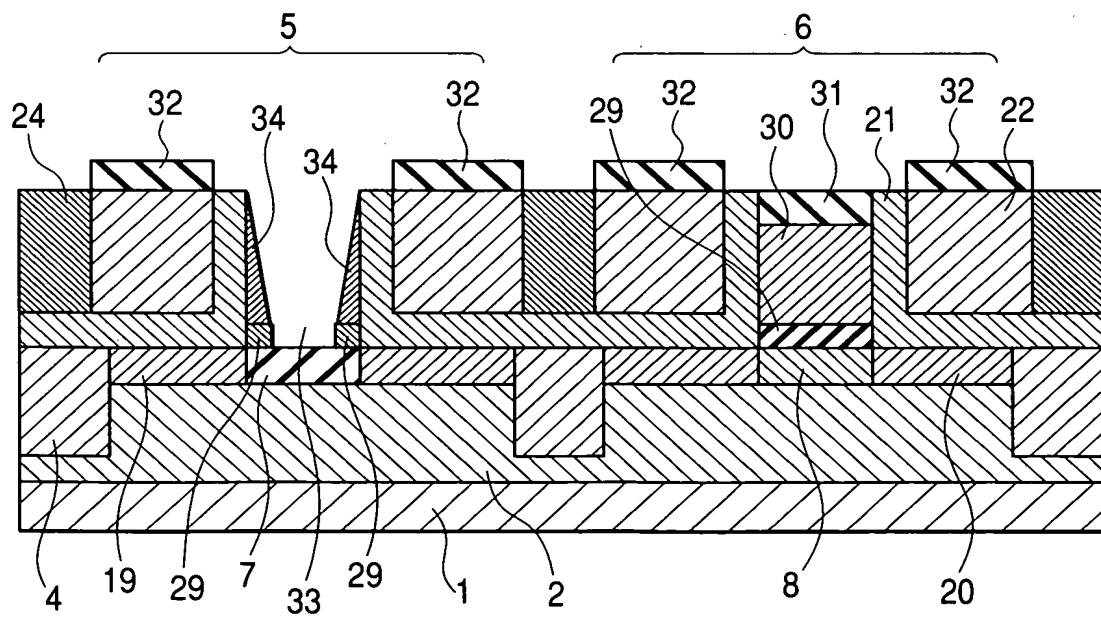
This diagram shows a cross-section of a semiconductor device with two identical unit regions, labeled 5 and 6. Region 5 includes components 31, 30, and 29. Region 6 includes components 29, 30, 31, and 21. The entire structure is built upon a substrate 1, which has a layer 2 on top. A layer 4 is at the bottom, with a patterned layer 7 above it. A layer 8 is located between the two unit regions. Other labels include 19, 20, and 22.

This cross-sectional view shows a semiconductor device with two main regions, 5 and 6, indicated by brackets at the top. Region 5 contains a stack of layers including a base layer 1, a layer 2, a layer 4, a layer 19, and a layer 7. A patterned layer 30 is formed on top of layer 7, with a layer 31 on top of it. A layer 29 is formed on top of layer 31. A layer 24 is formed on top of layer 29. Region 6 contains a stack of layers including a base layer 1, a layer 2, a layer 8, a layer 20, and a layer 21. A patterned layer 30 is formed on top of layer 21, with a layer 31 on top of it. A layer 29 is formed on top of layer 31. A layer 22 is formed on top of layer 29. The device is shown in a cross-sectional view with various layers and patterns indicated by different hatching patterns.

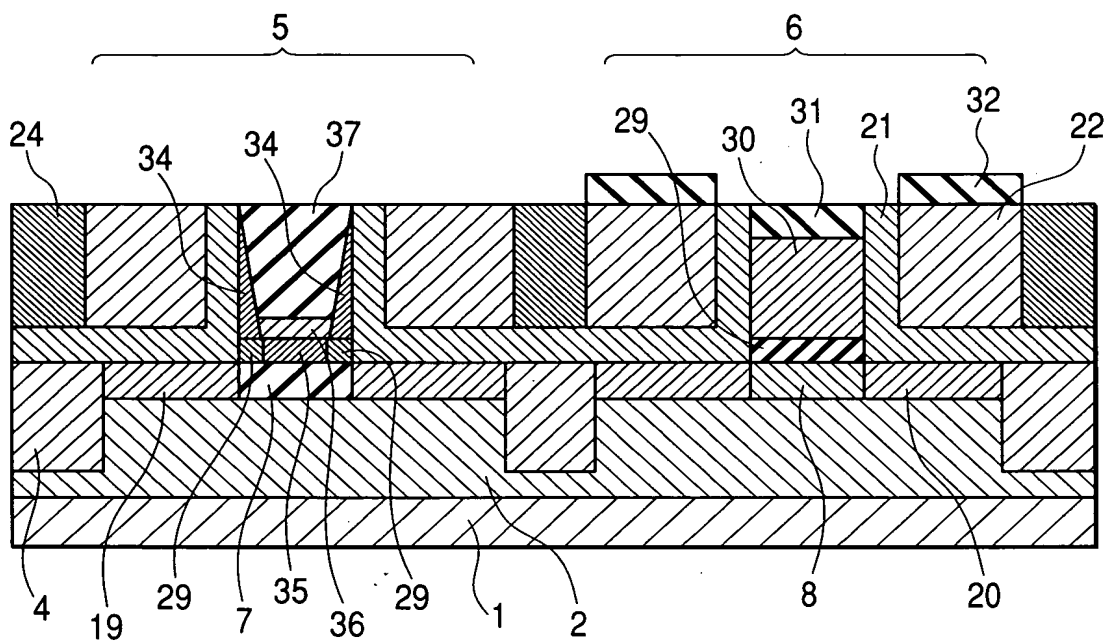
**FIG. 23**



**FIG. 24**



**FIG. 25**



**FIG. 26**

